DATASHEET

Description

The 9DBV0831 is a member of IDT's SOC-Friendly 1.8V Very-Low-Power (VLP) PCIe family. It can also be used for 50M or 125M Ethernet Applications via software frequency selection. The device has 8 output enables for clock management, and 3 selectable SMBus addresses.

Recommended Application

1.8V PCIe Gen1-2-3 Zero-Delay/Fan-out Buffer (ZDB/FOB)

Output Features

• 8 - 1-200Hz Low-Power (LP) HCSL DIF pairs w/Zo=100ohms

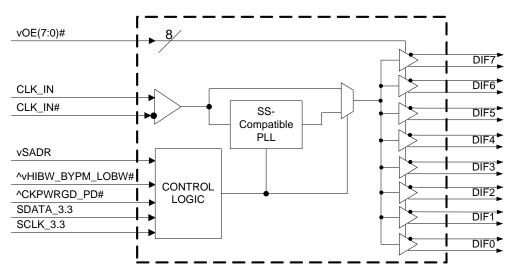
Key Specifications

- DIF cycle-to-cycle jitter <50ps
- DIF output-to-output skew <50ps
- DIF additive phase jitter is <100fs rms for PCIe Gen3
- DIF additive phase jitter <300fs rms for 12k-20MHz

Features/Benefits

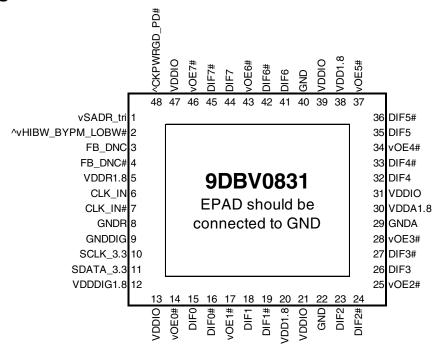
- LP-HCSL outputs save 16 resistors; minimal board space and BOM cost
- 62mW typical power consumption in PLL mode; minimal power consumption
- Spread Spectrum (SS) compatible; allows use of SS for EMI reduction
- OE# pins; support DIF power management
- HCSL compatible differential input; can be driven by common clock sources
- Programmable Slew rate for each output; allows tuning for various line lengths
- Programmable output amplitude; allows tuning for various application environments
- Pin/software selectable PLL bandwidth and PLL Bypass; minimize phase jitter for each application
- Outputs blocked until PLL is locked; clean system start-up
- Software selectable 50MHz or 125MHz PLL operation; useful for Ethernet applications
- Configuration can be accomplished with strapping pins; SMBus interface not required for device control
- 3.3V tolerant SMBus interface works with legacy controllers
- Space saving 48-pin 6x6mm VFQFPN; minimal board space
- Selectable SMBus addresses; multiple devices can easily share an SMBus segment

Block Diagram





Pin Configuration



48-pin VFQFPN, 6x6 mm, 0.4mm pitch

- ^v prefix indicates internal 120KOhm pull up AND pull down resistor (biased to VDD/2)
- v prefix indicates internal 120KOhm pull down resistor
- ^ prefix indicates internal 120KOhm pull up resistor

SMBus Address Selection Table

	SADR	Address	+ Read/Write bit
State of SADR on first application of	0	1101011	X
CKPWRGD_PD#	M	1101100	X
	1	1101101	Х

Power Management Table

CKPWRGD PD#	CLK IN SMBus		OEx# Pin	DIF	PLL		
CKFWKGD_FD#	CLK_IN	OEx bit	OEX# FIII	True O/P	Comp. O/P	1 LL	
0	X	Х	Х	Low	Low	Off	
1	Running	0	Х	Low	Low	On ¹	
1	Running	1	0	Running	Running	On ¹	
1	Running	1	1	Low	Low	On ¹	

^{1.} If Bypass mode is selected, the PLL will be off, and outputs will be running.



Power Connections

Pin Number			Description
VDD	VDDIO	GND	Description
			Input
5		8	receiver
			analog
12		9	Digital Power
20, 31, 38	13, 21, 31, 39, 47	22, 29, 40	DIF outputs
30		29	PLL Analog

Frequency Select Table

FSEL Byte3 [4:3]	CLK_IN (MHz)	DIFx (MHz)
00 (Default)	100.00	CLK_IN
01	50.00	CLK_IN
10	125.00	CLK_IN
11	Reserved	Reserved

PLL Operating Mode

HiBW_BypM_LoBW#	MODE	Byte1 [7:6] Readback	Byte1 [4:3] Control
0	PLL Lo BW	00	00
M	Bypass	01	01
1	PLL Hi BW	11	11



Pin Descriptions

PIN#	PIN NAME	TYPE	DESCRIPTION
4	VCADD +vi	LATCHED	Tri level letch to coloct CMDus Address Cos CMDus Address Coloction Toble
1	vSADR_tri	IN	Tri-level latch to select SMBus Address. See SMBus Address Selection Table.
2	^vHIBW BYPM LOBW#	LATCHED	Trilevel input to select High BW, Bypass or Low BW mode.
	^Vnibvv_b i Pivi_LObvv#	IN	See PLL Operating Mode Table for Details.
3	FB_DNC	DNC	True clock of differential feedback. The feedback output and feedback input are
3	FB_DINC	DINC	connected internally on this pin. Do not connect anything to this pin.
	ED DNO#	DNC	Complement clock of differential feedback. The feedback output and feedback
4	FB_DNC#	DNC	input are connected internally on this pin. Do not connect anything to this pin.
	VDDD4 0	DWD	1.8V power for differential input clock (receiver). This VDD should be treated as
5	VDDR1.8	PWR	an Analog power rail and filtered appropriately.
6	CLK_IN	IN	True Input for differential reference clock.
7	CLK_IN#	IN	Complementary Input for differential reference clock.
8	GNDR	GND	Analog Ground pin for the differential input (receiver)
9	GNDDIG	GND	Ground pin for digital circuitry
10	SCLK_3.3	IN	Clock pin of SMBus circuitry, 3.3V tolerant.
11	SDATA_3.3	I/O	Data pin for SMBus circuitry, 3.3V tolerant.
12	VDDDIG1.8	PWR	1.8V digital power (dirty power)
13	VDDIO	PWR	Power supply for differential outputs
14	vOE0#	IN	Active low input for enabling DIF pair 0. This pin has an internal pull-down.
'-			1 =disable outputs, 0 = enable outputs
15	DIF0	OUT	Differential true clock output
16	DIF0#	OUT	Differential Complementary clock output
17	vOE1#	IN	Active low input for enabling DIF pair 1. This pin has an internal pull-down.
			1 =disable outputs, 0 = enable outputs
18	DIF1	OUT	Differential true clock output
19	DIF1#	OUT	Differential Complementary clock output
20	VDD1.8	PWR	Power supply, nominal 1.8V
21	VDDIO	PWR	Power supply for differential outputs
22	GND	GND	Ground pin.
23	DIF2	OUT	Differential true clock output
24	DIF2#	OUT	Differential Complementary clock output
25	vOE2#	IN	Active low input for enabling DIF pair 2. This pin has an internal pull-down.
-00	DIEO	OUT	1 =disable outputs, 0 = enable outputs
26	DIF3	OUT	Differential true clock output
27	DIF3#	OUT	Differential Complementary clock output
28	vOE3#	IN	Active low input for enabling DIF pair 3. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs
29	GNDA	GND	Ground pin for the PLL core.
30	VDDA1.8	PWR	1.8V power for the PLL core.
31	VDDIO	PWR	Power supply for differential outputs
32	DIF4	OUT	Differential true clock output
33	DIF4#	OUT	Differential Complementary clock output
			Active low input for enabling DIF pair 4. This pin has an internal pull-down.
34	vOE4#	IN	1 =disable outputs, 0 = enable outputs
35	DIF5	OUT	Differential true clock output
36	DIF5#	OUT	Differential Complementary clock output
			Active low input for enabling DIF pair 5. This pin has an internal pull-down.
37	vOE5#	IN	1 =disable outputs, 0 = enable outputs
38	VDD1.8	PWR	Power supply, nominal 1.8V

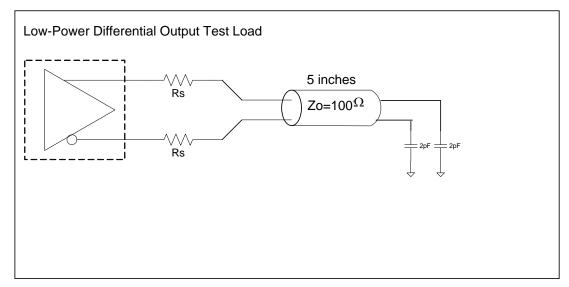


Pin Descriptions (cont.)

PIN#	PIN NAME	TYPE	DESCRIPTION	
39	VDDIO	PWR	Power supply for differential outputs	
40	GND	GND	Ground pin.	
41	DIF6	OUT	Differential true clock output	
42	DIF6#	OUT	Differential Complementary clock output	
43	vOE6#	IN	Active low input for enabling DIF pair 6. This pin has an internal pull-down.	
43	VOE0#	IIN	1 =disable outputs, 0 = enable outputs	
44	DIF7	OUT	Differential true clock output	
45	DIF7#	OUT	Differential Complementary clock output	
46	vOE7#	IN	Active low input for enabling DIF pair 7. This pin has an internal pull-down.	
40	VOE7#	IIN	1 =disable outputs, 0 = enable outputs	
47	VDDIO	PWR	Power supply for differential outputs	
			Input notifies device to sample latched inputs and start up on first high	
48	^CKPWRGD_PD#	IN	assertion. Low enters Power Down Mode, subsequent high assertions exit	
	Power Down Mode. This pin has internal pull-up resistor.			
49	EPAD	GND	Connect to Ground	



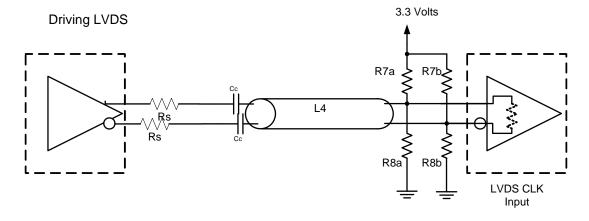
Test Loads



Alternate Differential Output Terminations

Rs	Zo	Units
33	100	Ohms
27	85	Offilis

Driving LVDS



Driving LVDS inputs with the 9DBV0831

Dirting Lt DO mp	Briving Evbo inputs with the 3bbv 0001					
	,	Value				
	Receiver has					
Component	termination	have termination	Note			
R7a, R7b	10K ohm	140 ohm				
R8a, R8b	5.6K ohm	75 ohm				
Cc	0.1 uF	0.1 uF				
Vcm	1.2 volts	1.2 volts				



Absolute Maximum Ratings

Stresses above the ratings listed below can cause permanent damage to the 9DBV0831. These ratings, which are standard values for IDT commercially rated parts, are stress ratings only. Functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods can affect product reliability. Electrical parameters are guaranteed only over the recommended operating temperature range.

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx		-0.5		2.5	V	1,2
Input Voltage	V_{IN}		-0.5		V _{DD} +0.5	V	1,3
Input High Voltage, SMBus	V_{IHSMB}	SMBus clock and data pins			3.6	V	1
Storage Temperature	Ts		-65		150	ô	1
Junction Temperature	Tj				125	ç	1
Input ESD protection	ESD prot	Human Body Model	2000			٧	1

¹Guaranteed by design and characterization, not 100% tested in production.

Electrical Characteristics-Clock Input Parameters

TA = T_{AMB} Supply Voltages per normal operation conditions. See Test Loads for Loading Conditions

TAMB, Supply Voltages per hermal operation containers, god feet Leader for Leading Containers							
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Input Common Mode Voltage - DIF_IN	V _{COM}	Common Mode Input Voltage	200		725	mV	1
Input Swing - DIF_IN	V _{SWING}	Differential value	300		1450	mV	1
Input Slew Rate - DIF_IN	dv/dt	Measured differentially	0.4		8	V/ns	1,2
Input Leakage Current	I _{IN}	$V_{IN} = V_{DD}$, $V_{IN} = GND$	-5		5	uA	
Input Duty Cycle	d _{tin}	Measurement from differential wavefrom	45	50	55	%	1
Input Jitter - Cycle to Cycle	J_{DIFIn}	Differential Measurement	0		150	ps	1

¹ Guaranteed by design and characterization, not 100% tested in production.

² Operation under these conditions is neither implied nor guaranteed.

³ Not to exceed 2.5V.

² Slew rate measured through +/-75mV window centered around differential zero



Electrical Characteristics-Input/Supply/Common Parameters-Normal Operating Conditions

TA = T_{AMB}, Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Supply Voltage	VDDx	Supply voltage for core and analog	1.7	1.8	1.9	V	
Output Supply Voltage	VDDIO	Supply voltage for Low Power HCSL Outputs	0.95	1.05	1.9	V	
Ambient Operating	T _{AMB}	Commmercial range	0	25	70	°C	
Temperature	' AMB	Industrial range	-40	25	85	V	
Input High Voltage	V _{IH}	Single-ended inputs, except SMBus	0.75 V _{DD}		$V_{DD} + 0.3$	V	
Input Mid Voltage	V_{IM}	Single-ended tri-level inputs ('_tri' suffix)	0.4 V _{DD}		0.6 V _{DD}	V	
Input Low Voltage	V _{IL}	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V	
	I _{IN}	Single-ended inputs, $V_{IN} = GND$, $V_{IN} = VDD$	-5		5	uA	
Input Current	I _{INP}	$Single-ended inputs \\ V_{IN} = 0 \text{ V}; \text{ Inputs with internal pull-up resistors} \\ V_{IN} = \text{VDD}; \text{ Inputs with internal pull-down resistors}$	-200		200	uA	
	F _{ibyp}	Bypass mode	1		200	MHz	2
Innut Fraguency	F _{ipII}	100MHz PLL mode	60	100.00	140	MHz	2
Input Frequency	F_{ipll}	125MHz PLL mode	75	125.00	175	V °C °C V V V UA WHz MHz MHz MHz MHz MHz HP PF PF TS V V V V V V V V V V V Clocks V V V V V T NS	2
	F_{ipll}	50MHz PLL mode	30	50.00	65	MHz	2
Pin Inductance	L_{pin}				7	nΗ	1
	C _{IN}	Logic Inputs, except DIF_IN	1.5		5	рF	1
Capacitance	C _{INDIF_IN}	DIF_IN differential clock inputs	1.5		2.7	pF pF	1,5
	C _{OUT}	Output pin capacitance			6 pF	1	
Clk Stabilization	T _{STAB}	From V _{DD} Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock			1	ms	1,2
Input SS Modulation Frequency PCIe	f _{MODINPCle}	Allowable Frequency for PCIe Applications (Triangular Modulation)	30		33	kHz	
Input SS Modulation Frequency non-PCle	f _{MODIN}	Allowable Frequency for non-PCIe Applications (Triangular Modulation)	0		66	kHz	
OE# Latency	t _{LATOE#}	DIF start after OE# assertion DIF stop after OE# deassertion	1		3	clocks	1,3
Tdrive_PD#	t _{DRVPD}	DIF output enable after PD# de-assertion			300	us	1,3
Tfall	t _F	Fall time of single-ended control inputs			5	ns	2
Trise	t _R	Rise time of single-ended control inputs			5	ns	2
SMBus Input Low Voltage	V_{ILSMB}	$V_{DDSMB} = 3.3V$, see note 4 for $V_{DDSMB} < 3.3V$			0.6	V	
SMBus Input High Voltage	V _{IHSMB}	$V_{DDSMB} = 3.3V$, see note 5 for $V_{DDSMB} < 3.3V$	2.1		3.6		4
SMBus Output Low Voltage	V_{OLSMB}	@ I _{PULLUP}			0.4	V	
SMBus Sink Current	I _{PULLUP}	@ V _{OL}	4			mA	
Nominal Bus Voltage	$V_{\rm DDSMB}$	Bus Voltage	1.7		3.6	V	
SCLK/SDATA Rise Time	t _{RSMB}	(Max VIL - 0.15) to (Min VIH + 0.15)			1000	ns	1
SCLK/SDATA Fall Time	t _{FSMB}	(Min VIH + 0.15) to (Max VIL - 0.15)			300	ns	1
SMBus Operating Frequency	f _{MAXSMB}	Maximum SMBus operating frequency			400	kHz	6

¹Guaranteed by design and characterization, not 100% tested in production.

²Control input must be monotonic from 20% to 80% of input swing.

³Time from deassertion until outputs are >200 mV

 $^{^{4}}$ For $V_{DDSMB} < 3.3V$, $V_{IHSMB} >= 0.8xV_{DDSMB}$

⁵DIF IN input

⁶The differential input clock must be running for the SMBus to be active



Electrical Characteristics-Low Power HCSL Outputs

TA = T_{COM} or T_{IND}; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

		•	-				
PARAMETER	SYMBOL	CONDITIONS		TYP	MAX	UNITS	NOTES
Slew rate	dV/dt	Scope averaging on, fast setting	1.7	2.7	4	V/ns	1,2,3
Siew rate	dV/dt	Scope averaging on, slow setting	1.2	2.1	3.3	V/ns	1,2,3
Slew rate matching	∆dV/dt	Slew rate matching, Scope averaging on		4.6	20	%	1,2,4
Voltage High	V_{HIGH}	Statistical measurement on single-ended signal using oscilloscope math function. (Scope	660	774	850	mV	7
Voltage Low	V_{LOW}	averaging on)	-150	18	150	1110	7
Max Voltage	Vmax	Measurement on single ended signal using		820	1150	mV	7
Min Voltage	Vmin	absolute value. (Scope averaging off)	-300	-25		IIIV	7
Vswing	Vswing	Scope averaging off	300	1528		mV	1,2
Crossing Voltage (abs)	Vcross_abs	Scope averaging off	250	413	550	mV	1,5
Crossing Voltage (var)	Δ-Vcross	Scope averaging off		11	140	mV	1,6

¹Guaranteed by design and characterization, not 100% tested in production.

Electrical Characteristics-Current Consumption

TA = T_{COM} or T_{IND}; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

COM THE TT							
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
Operating Supply Current	I _{DDA}	VDDA+VDDR, PLL Mode, @100MHz		11	15	mA	
	I _{DD}	VDD, All outputs active @100MHz		7	10	mA	
	I _{DDO}	VDDO, All outputs active @100MHz		28	35	mA	
	I _{DDAPD}	VDDA+VDDR, PLL Mode, @100MHz		0.6	1	mA	2
Powerdown Current	I _{DDPD}	VDD, Outputs Low/Low		1	2	mA	2
	I _{DDOPD}	VDDO,Outputs Low/Low		0	0.01	mA	2

¹ Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform

³ Slew rate is measured through the Vswing voltage range centered around differential 0V. This results in a +/-150mV window around differential 0V

⁴ Matching applies to rising edge rate for Clock and falling edge rate for Clock#. It is measured using a +/-75mV window centered on the average cross point where Clock rising meets Clock# falling. The median cross point is used to calculate the voltage thresholds the oscilloscope is to use for the edge rate calculations.

⁵ Vcross is defined as voltage where Clock = Clock# measured on a component test board and only applies to the differential rising edge (i.e. Clock rising and Clock# falling).

⁶ The total variation of all Vcross measurements in any particular system. Note that this is a subset of Vcross_min/max (Vcross absolute) allowed. The intent is to limit Vcross induced modulation by setting Δ-Vcross to be smaller than Vcross absolute.

⁷ At default SMBus settings.

² Input clock stopped.



Electrical Characteristics-Output Duty Cycle, Jitter, Skew and PLL Characteristics

TA = T_{COM} or T_{IND}; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	NOTES
PLL Bandwidth	BW	-3dB point in High BW Mode	2	2.7	4	MHz	1,5
PLL Bandwidth	DVV	-3dB point in Low BW Mode	1	1.4	2	MHz	1,5
PLL Jitter Peaking	t _{JPEAK}	Peak Pass band Gain		1.1	2	dB	1
Duty Cycle	t _{DC}	Measured differentially, PLL Mode	45	50.1	55	%	1
Duty Cycle Distortion	t _{DCD}	Measured differentially, Bypass Mode @100MHz	-1	0.02	1	%	1,3
Ckow Input to Output	t _{pdBYP}	Bypass Mode, V _T = 50%	3000	3636	4400	ps	1
Skew, Input to Output	t _{pdPLL}	PLL Mode V _T = 50%	0	81	200	ps	1,4
Skew, Output to Output	t _{sk3}	V _T = 50%		29	50	ps	1,4
Jitter, Cycle to cycle	+.	PLL mode		13.0	50	ps	1,2
Jitter, Cycle to Cycle	t _{jcyc-cyc}	Additive Jitter in Bypass Mode		0.1	25	ps	1,2

¹ Guaranteed by design and characterization, not 100% tested in production.

Electrical Characteristics-Phase Jitter Parameters

 $TA = T_{COM}$ or T_{IND} ; Supply Voltages per normal operation conditions, See Test Loads for Loading Conditions

						INDUSTRY		
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	LIMIT	UNITS	Notes
	t _{jphPCleG1}	PCIe Gen 1		33	52	86	ps (p-p)	1,2,3,5
		PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.9	1.4	3	ps (rms)	1,2,3,5
Phase Jitter, PLL Mode	t _{jphPCleG2}	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		2.1	2.5	3.1	ps (rms)	1,2,3,5
	t _{jphPCleG3}	PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		0.5	0.6	1	ps (rms)	1,2,3,5
	t _{jphSGMII}	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		0.0	2.0	NA	ps (rms)	1,6
	t _{jphPCleG1}	PCIe Gen 1		0.1	2.4	N/A	ps (p-p)	1,2,3,5
		PCIe Gen 2 Lo Band 10kHz < f < 1.5MHz		0.1	0.4	N/A	ps (rms)	1,2,3,4, 5
Additive Phase Jitter, Bypass Mode	t _{jphPCleG2}	PCIe Gen 2 High Band 1.5MHz < f < Nyquist (50MHz)		0.1	0.1	N/A	ps (rms)	1,2,3,4
	t _{jphPCleG3}	PCIe Gen 3 (PLL BW of 2-4 or 2-5MHz, CDR = 10MHz)		165	200	N/A	ps (rms)	1,2,3,4
	t _{jphSGMII}	125MHz, 1.5MHz to 10MHz, -20dB/decade rollover < 1.5MHz, -40db/decade rolloff > 10MHz		251	300	N/A	fs (rms)	1,6

¹Guaranteed by design and characterization, not 100% tested in production.

² Measured from differential waveform

³ Duty cycle distortion is the difference in duty cycle between the output and the input clock when the device is operated in bypass mode.

⁴ All outputs at default slew rate

⁵ The MIN/TYP/MAX values of each BW setting track each other, i.e., Low BW MAX will never occur with Hi BW MIN.

² See http://www.pcisig.com for complete specs

³ Sample size of at least 100K cycles. This figures extrapolates to 108ps pk-pk @ 1M cycles for a BER of 1-12.

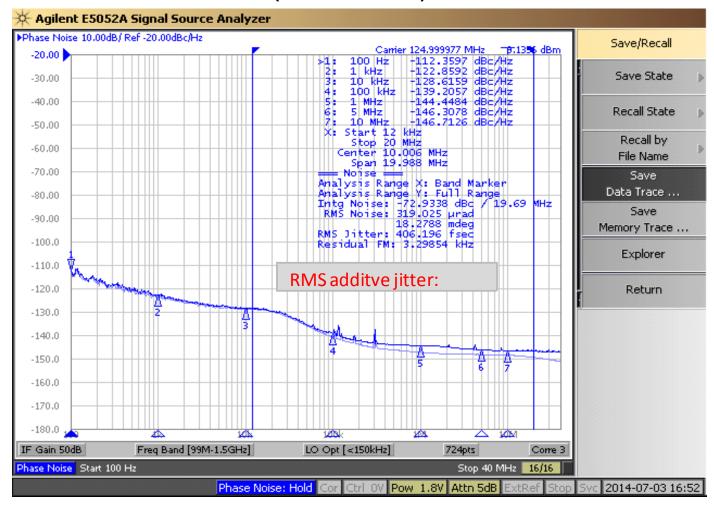
⁴ For RMS figures, additive jitter is calculated by solving the following equation: Additive jitter = SQRT[(total jitter)^2 - (input jitter)^2]

⁵ Driven by 9FGV0831 or equivalent

⁶ Driven by Rohde&Schwarz SMA100



Additive Phase Jitter Plot: 125M (12kHz to 20MHz)





General SMBus Serial Interface Information

How to Write

- Controller (host) sends a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) sends the byte count = X
- IDT clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- IDT clock will acknowledge each byte one at a time
- Controller (host) sends a Stop bit

	Index Blo	ock V	Vrite Operation
Control	ler (Host)		IDT (Slave/Receiver)
Т	starT bit		
Slave	Address		
WR	WRite		
			ACK
Beginnin	g Byte = N		
			ACK
Data Byte	e Count = X] [
			ACK
Beginni	ng Byte N		
			ACK
0		$ \times $	
0		X Byte	0
0		Ф	0
			0
Byte N	N + X - 1		
			ACK
Р	stoP bit		

Note: SMBus address is latched on SADR pin.

How to Read

- Controller (host) will send a start bit
- Controller (host) sends the write address
- IDT clock will acknowledge
- Controller (host) sends the beginning byte location = N
- IDT clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- IDT clock will acknowledge
- IDT clock will send the data byte count = X
- IDT clock sends Byte N+X-1
- IDT clock sends Byte 0 through Byte X (if X_(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- · Controller (host) will send a stop bit

	Index Block Read Operation							
Co	ntroller (Host)		IDT (Slave/Receiver)					
Т	starT bit							
S	Slave Address							
WR	WRite							
			ACK					
Beg	inning Byte = N							
			ACK					
RT	Repeat starT							
S	lave Address							
RD	ReaD							
			ACK					
			Data Byte Count=X					
	ACK							
			Beginning Byte N					
	ACK							
		e)	0					
	0	X Byte	0					
	0	×	0					
	0							
			Byte N + X - 1					
N	Not acknowledge							
Р	stoP bit							



SMBus Table: Output Enable Register ¹

Byte 0	Name	Control Function	Туре	0	1	Default
Bit 7	DIF OE7	Output Enable	RW	Low/Low	Enabled	1
Bit 6	DIF OE6	Output Enable	RW	Low/Low	Enabled	1
Bit 5	DIF OE5	Output Enable	RW	Low/Low	Enabled	1
Bit 4	DIF OE4	Output Enable	RW	Low/Low	Enabled	1
Bit 3	DIF OE3	Output Enable	RW	Low/Low	Enabled	1
Bit 2	DIF OE2	Output Enable	RW	Low/Low	Enabled	1
Bit 1	DIF OE1	Output Enable	RW	Low/Low	Enabled	1
Bit 0	DIF OE0	Output Enable	RW	Low/Low	Enabled	1

^{1.} A low on these bits will overide the OE# pin and force the differential output Low/Low

SMBus Table: PLL Operating Mode and Output Amplitude Control Register

Byte 1	Name	Control Function	Туре	0	1	Default
Bit 7	PLLMODERB1	PLL Mode Readback Bit 1	R	See PLL Operating Mode Table		Latch
Bit 6	PLLMODERB0	PLL Mode Readback Bit 0	R	Gee i LL Operat	ing wode rable	Latch
Bit 5	PLLMODE SWCNTRL	Enable SW control of PLL Mode	RW	Values in B1[7:6]	Values in B1[4:3]	0
DIL 3	I LEWIODE_SWONTKE	Lilable 3W control of 1 EL Wode	1744	set PLL Mode	set PLL Mode	U
Bit 4	PLLMODE1	PLL Mode Control Bit 1	RW ¹	See PLL Operat	ing Mode Table	0
Bit 3	PLLMODE0	PLL Mode Control Bit 0	RW ¹	See FLL Operat	ing wode rable	0
Bit 2		Reserved				1
Bit 1	AMPLITUDE 1	Controls Output Amplitude	RW	00 = 0.6V	01 = 0.7V	1
Bit 0	AMPLITUDE 0	Controls Output Amplitude	RW	10= 0.8V	11 = 0.9V	0

^{1.} B1[5] must be set to a 1 for these bits to have any effect on the part.

SMBus Table: DIF Slew Rate Control Register

Byte 2	Name	Control Function	Type	0	1	Default
Bit 7	SLEWRATESEL DIF7	Adjust Slew Rate of DIF7	RW	Slow Setting	Fast Setting	1
Bit 6	SLEWRATESEL DIF6	Adjust Slew Rate of DIF6	RW	Slow Setting	Fast Setting	1
Bit 5	SLEWRATESEL DIF5	Adjust Slew Rate of DIF5	RW	Slow Setting	Fast Setting	1
Bit 4	SLEWRATESEL DIF4	Adjust Slew Rate of DIF4	RW	Slow Setting	Fast Setting	1
Bit 3	SLEWRATESEL DIF3	Adjust Slew Rate of DIF3	RW	Slow Setting	Fast Setting	1
Bit 2	SLEWRATESEL DIF2	Adjust Slew Rate of DIF2	RW	Slow Setting	Fast Setting	1
Bit 1	SLEWRATESEL DIF1	Adjust Slew Rate of DIF1	RW	Slow Setting	Fast Setting	1
Bit 0	SLEWRATESEL DIF0	Adjust Slew Rate of DIF0	RW	Slow Setting	Fast Setting	1

SMBus Table: Frequency Select Control Register

Smbus Table. Frequency Select Control Register									
Byte 3	Name	Control Function	Type	0	1	Default			
Bit 7		Reserved				1			
Bit 6	Reserved								
Bit 5	FREQ SEL EN	Enable SW selection of	RW	SW frequency	SW frequency	0			
ысэ	TREQ_OLL_EN	frequency	1200	change disabled	change enabled	J			
Bit 4	FSEL1	Freq. Select Bit 1	RW ¹	See Frequency	, Salact Table	0			
Bit 3	FSEL0	Freq. Select Bit 0	RW ¹	See Hequency	y Select Table	0			
Bit 2		Reserved	•			1			
Bit 1	Reserved					1			
Bit 0	SLEWRATESEL FB	Adjust Slew Rate of FB	RW	2.0V/ns	3.0V/ns	1			

^{1.} B3[5] must be set to a 1 for these bits to have any effect on the part.

Byte 4 is Reserved and reads back 'hFF



SMBus Table: Revision and Vendor ID Register

Byte 5	Name	Control Function	Туре	0	1	Default
Bit 7	RID3		R		0	
Bit 6	RID2	Revision ID	R	A rev =	0	
Bit 5	RID1		R	A lev =	0	
Bit 4	RID0		R		0	
Bit 3	VID3		R			0
Bit 2	VID2	VENDOR ID	R	0001	0001 = IDT	
Bit 1	VID1	VENDOR ID	R	- 0001 = ID1		0
Bit 0	VID0		R			1

SMBus Table: Device Type/Device ID

Byte 6	Name	Control Function	Туре	0	1	Default
Bit 7	Device Type1	Device Type	R	00 = FGx,	01 = DBx,	0
Bit 6	Device Type0	Device Type	R	10 = DMx, 1	1	
Bit 5	Device ID5		R			0
Bit 4	Device ID4	1	R			0
Bit 3	Device ID3	Device ID	R	001000 bina	n, or 08 hov	1
Bit 2	Device ID2	Device ib	R	001000 billa	ily of oo flex	0
Bit 1	Device ID1		R			
Bit 0	Device ID0	1	R			0

SMBus Table: Byte Count Register

Byte 7	Name	Control Function	Туре	0	1	Default
Bit 7		Reserved				0
Bit 6	Reserved					0
Bit 5	Reserved					0
Bit 4	BC4		RW			0
Bit 3	BC3		RW	Writing to this regist	er will configure how	1
Bit 2	BC2	Byte Count Programming	RW	many bytes will be i	read back, default is	0
Bit 1	BC1		RW	= 8 b	ytes.	0
Bit 0	BC0		RW			0



Marking Diagrams

ICS
DBV0831AL
YYWW
COO
LOT



Notes:

- 1. "LOT" is the lot sequence number.
- 2. "COO" denotes country of origin.
- 3. YYWW is the last two digits of the year and week that the part was assembled.
- 4. Line 2: truncated part number
- 5. "L" denotes RoHS compliant package.
- 6. "I" denotes industrial temperature range device.

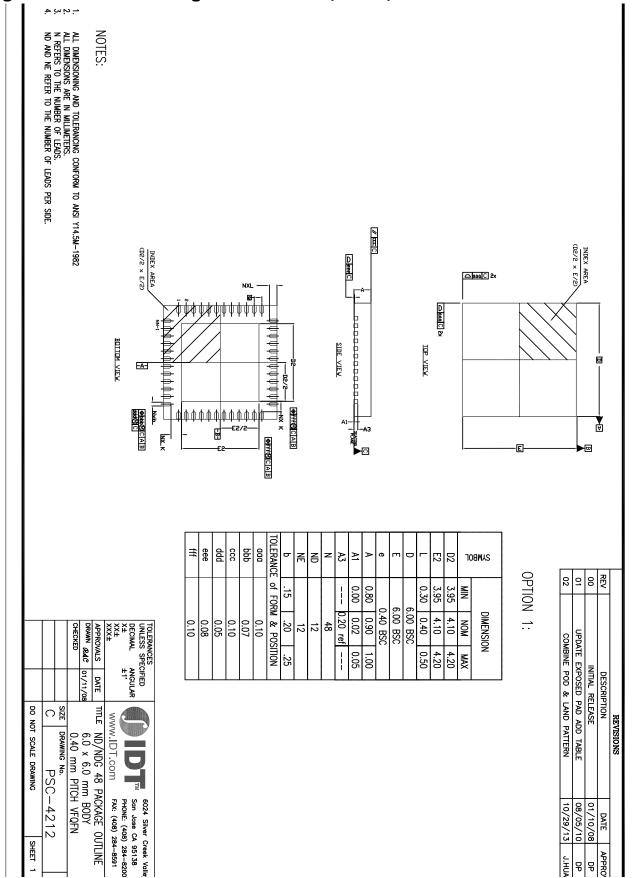
Thermal Characteristics

PARAMETER	SYMBOL	CONDITIONS	PKG	TYP VALUE	UNITS	NOTES
	$\theta_{\sf JC}$	Junction to Case	NDG48 33 2.1 37 30 27 26	33	°C/W	1
	θ_{Jb}	Junction to Base		2.1	°C/W	1
Thermal Resistance	θ_{JA0}	Junction to Air, still air		37	°C/W	1
Thermal Resistance	θ_{JA1}	Junction to Air, 1 m/s air flow		°C/W	1	
	θ_{JA3}	Junction to Air, 3 m/s air flow		°C/W	1	
	θ_{JA5}	Junction to Air, 5 m/s air flow		26	°C/W	1

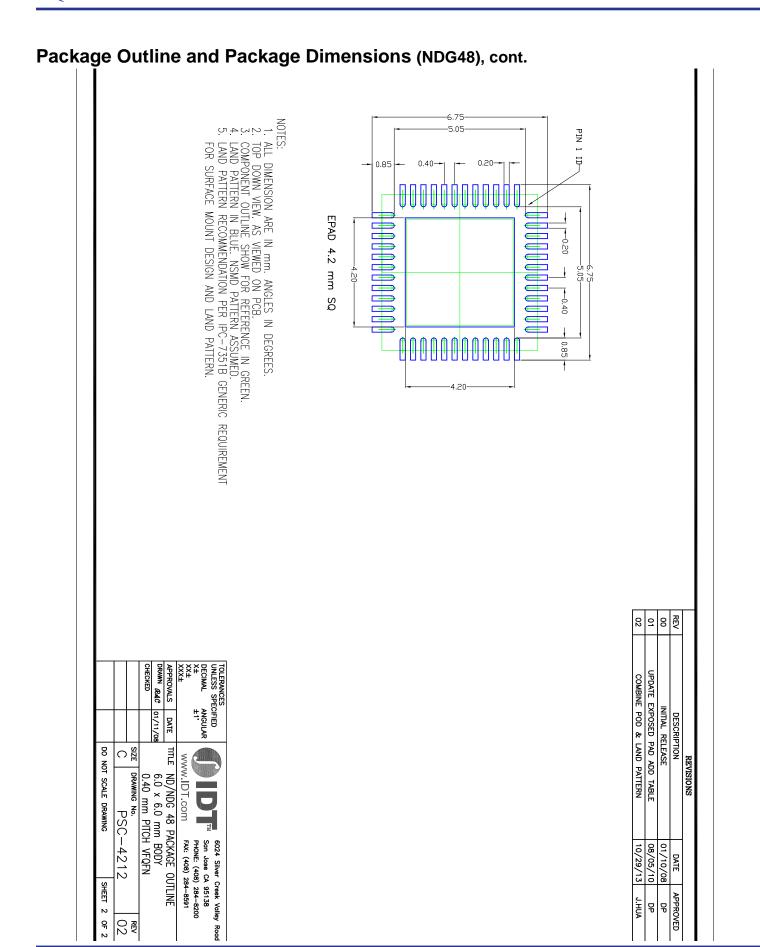
¹ePad soldered to board



Package Outline and Package Dimensions (NDG48)









Ordering Information

Part / Order Number	Shipping Packaging	Package	Temperature
9DBV0831AKLF	Trays	48-pin VFQFPN	0 to +70° C
9DBV0831AKLFT	Tape and Reel	48-pin VFQFPN	0 to +70° C
9DBV0831AKILF	Trays	48-pin VFQFPN	-40 to +85° C
9DBV0831AKILFT	Tape and Reel	48-pin VFQFPN	-40 to +85° C

[&]quot;LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

Revision History

Rev.	Issue Date	Initiator	Description	Page #
A	3/22/21012	RDW	 Updated electrical tables with typical data from characterization. Updated ordering information to indicate B rev device. Data sheet title change to indicate PCle Gen1/2/3. Move to preliminary. 	
В	7/6/2012	RDW	Extensive changes to page 1 text: Description, Recommended Application, Output Features, Features/Benefits, DS Title. Indicated default value in Frequency Select Table. Pins 3,4 changed from FB,FB# to FB_DNC,FB_DNC# to indicate that these pins are Do Not Connect (DNC).	
С	7/10/2012	RDW	Removed 156.25M from input frequency specification.	
D	8/13/2012	RDW	1. Removed "Differential" from DS title and Recommended Application, corrected typo's in Description. 2. Removed references to 60KOhm pulldown under pinout. 3. Updated "Phase Jitter Parameters" table by adding "Industry Limit" column and updated all Electrical Tables with characterization data. 4. Updated Byte3[0] to be consistent with Byte 2. Updated Byte6[7:6] definition. 5. Updated Mark spec with correct part revision (A) and added thermal data to page 13. 6. Added NDG48 to "Package Outline and Package Dimensions" on page 14 and updated Ordering information to correct part revision (A rev). 7. Move to final.	1,2,6- 9,11,13,14
Е	2/25/2013	RDW	1. Changed VIH min. from 0.65*VDD to 0.75*VDD 2. Changed VIL max. from 0.35*VDD to 0.25*VDD 3. Added missing mid-level input voltage spec (VIM) of 0.4*VDD to 0.6*VDD.	7
F	8/12/2014	RDW	Changed package designator from "MLF" to "VFQFPN"	Various
G	3/2/2015	RDW	 Minor formatting updates to electrical tables Added callout for EPAD Updated block diagram to latest format. Updated front page text to latest format. Added additive phase jitter plot. Corrected Byte 2 and Byte 5 in SMBus. 	Various
Н	4/28/2016	RDW	Updated max frequency of 100MHz PLL mode to 140MHz Updated max frequency of 125MHz PLL mode to 175MHz Updated max frequency of 50MHz PLL mode to 65MHz	8

[&]quot;A" is the device revision designator (will not correlate with the datasheet revision).



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